

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1169** is a Common Emitter Device Designed for Class C Amplifier Applications in HF Land Mobile Radios.

FEATURES INCLUDE:

- Aluminum Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	6 A
V_{CB}	36 V
P_{DISS}	80 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
q_{JC}	2.2 °C/W

PACKAGE STYLE .500 4L STUD

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25.65	1.050/26.67
B	.220/5.59	.230/5.84
C	.495/12.57	.505/12.83
D	.003/0.08	.007/0.18
E	.160/4.06	.180/4.57
F	.622/15.80	
G	.100/2.54	.130/3.31
H	.415/10.54	.425/10.80
I	.720/18.29	
J	.250/6.35	.290/7.37

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100mA	18			V
BV_{CEO}	I _C = 50mA	36			V
BV_{EBO}	I _E = 10mA	4.0			V
I_{CB0}	V _{CB} = 15 V			5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	5			---
C_{OB}	V _{CB} = 12.5 V f = 1.0 MHz			200	pF
G_{PE} h_C	V _{CE} = 12.5 V P _{OUT} = 40 W f = 88 MHz	6.0	7.5 65		dB %